











**TS3DV642** 

SCDS343F -MAY 2013 - REVISED AUGUST 2018

RDV642 12-Channol 1:2 MIIY/DEMILY with 1.8 V Compatible Control

# TS3DV642 12-Channel 1:2 MUX/DEMUX with 1.8 V Compatible Control and Power-Down Mode

## 1 Features

Switch Type: 2:1 or 1:2

Dynamic Characteristics

Differential Bandwidth ( –3 dB)

- Port A: 6.9 GHz Typical

Port B: 7.5 GHz Typical

Crosstalk (at 1.7 GHz): –40 dB

Isolation (at 1.7 GHz): –23 dB

Insertion Loss (DC)

- Port A: -0.75 dB

Port B: -1.0 dB

Return Loss (at 1.7 GHz): –15.9 dB

Intra-Pair (Bit-Bit) Skew

Port A: 2 psPort B: 6 ps

- R<sub>ON</sub>

Port A: 6.5 ΩPort B: 8.2 Ω

C<sub>ON</sub> at 1 GHz: 0.5 pF (Typical)

V<sub>CC</sub> Range: 2.6 V to 4.5 V
I/O Voltage Range: 0 V to 5 V

Special Features

 I<sub>OFF</sub> Protection Prevents Current Leakage in Powered Down State (V<sub>CC</sub> = 0 V)

ESD Performance

- 2-kV Human Body Model (A114B, Class II)

1-kV Charged Device Model (C101)

42-pin WQFN Package (9 mm x 3.5 mm, 0.5 mm pitch)

## 2 Applications

- HDMI 2.0 With Support for 4k2k up to 60 Hz
- DVI 1.0 Signal Switching
- DisplayPort 1.4 Signal Switching
- General Purpose TMDS Signal Switching
- General Purpose LVDS Signal Switching
- General Purpose High-Speed Signal Switching

#### 3 Description

The TS3DV642 is a 12 channel 1:2 or 2:1 bidirectional multiplexer/demultiplexer. The TS3DV642 operates from a 2.6 V to 4.5 V supply, making it suitable for battery-powered applications. It offers low and flat on-state resistance ( $R_{ON}$ ) as well as low I/O capacitance which allows it to achieve a typical bandwidth of up to 7.5 GHz. The device provides the high bandwidth necessary for HDMI and DisplayPort applications.

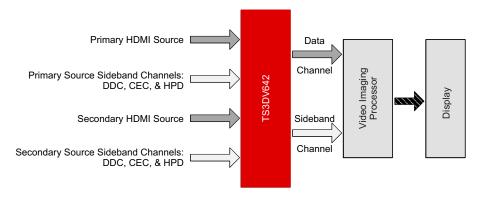
The TS3DV642 offers a power-down mode, in which all channels become Hi-Z and the device operates with minimal power.

#### Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
TS3DV642	WQFN (42)	9.00 mm × 3.50 mm		

(1) For all available packages, see the orderable addendum at the end of the datasheet.

#### Simplified Schematic





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## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Cł	nanges from Revision E (June 2017) to Revision F	Page
<u>.</u>	Changed Figure 27, removed capacitors	21
Cł	nanges from Revision D (December 2015) to Revision E	Page
•	Changed Application From: DisplayPort 1.2a Signal Switching To: DisplayPort 1.4 Signal Switching	1
•	Added Test Condition of 4.05 GHZ at -35 dB to Xtalk in the <i>Dynamic Characteristics</i> table	8
<u>.</u>	Added Test Condition of 4.05 GHZ at -25 dB to OISO in the <i>Dynamic Characteristics</i> table	8
Cł	nanges from Revision C (November 2014) to Revision D	Page
•	Changed the storage temperature to the Absolute Maximum Ratings table	6
Cł	nanges from Revision B (August 2013) to Revision C	Page
•	Added Handling Rating table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.	1
•	Deleted row from ABS MAX table: Package thermal impedance	6
•	Added the Handling Ratings table, deleted the T <sub>stg</sub> row Absolute Maximum ratings table and added to Handling Ratings table.	6

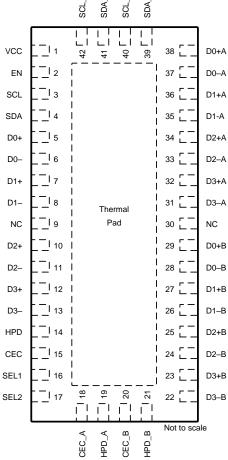


C	hanges from Revision A (July 2013) to Revision B	Page
•	Changed Application From: HDMI 1.4/DVI 1.0 Signal Switching To: HDMI 1.4b with support for 4k2k up to 30 Hz	·
•	Added Application: DVI 1.0 Signal Switching	·
•	Changed Application From: DisplayPort 1.2 Signal Switching To: DisplayPort 1.2a Signal Switching	
•	Added Eye Pattern and Time Interval Error Histogram graphics, Figure 10 to Figure 13	10



## 5 Pin Configuration and Functions

RUA Package
42 Pin WQFN With Exposed Thermal Pad
Top View



## **Pin Functions**

	PIN	TVDE	DESCRIPTION
NAME	NO.	TYPE	DESCRIPTION
VCC	1	Power	Supply Voltage
SEL1	16	1	Select Input 1
SEL2	17	1	Select Input 2
EN	2	1	Output Enable
D0+A	38	I/O	Port A, Channel 0, +ve signal
D0-A	37	I/O	Port A, Channel 0, -ve signal
D1+A	36	I/O	Port A, Channel 1, +ve signal
D1-A	35	I/O	Port A, Channel 1, -ve signal
D2+A	34	I/O	Port A, Channel 2, +ve signal
D2-A	33	I/O	Port A, Channel 2,-ve signal
D3+A	32	I/O	Port A, Channel 3, +ve signal
D3-A	31	I/O	Port A, Channel 3, -ve signal
SCL_A	42	I/O	Port A, DDC Clock
SDA_A	41	I/O	Port A, DDC Data



## Pin Functions (continued)

PIN					
NAME	NO.	TYPE	DESCRIPTION		
HPD_A	19	I/O	Port A, Hot Plug Detects		
CEC_A	18	I/O	Port A, Consumer Electronics Control		
D0+B	29	I/O	Port B, Channel 0, +ve signal		
D0-B	28	I/O	Port B, Channel 0, -ve signal		
D1+B	27	I/O	Port B, Channel 1, +ve signal		
D1-B	26	I/O	Port B, Channel 1, -ve signal		
D2+B	25	I/O	Port B, Channel 2, +ve signal		
D2-B	24	I/O	Port B, Channel 2,-ve signal		
D3+B	23	I/O	Port B, Channel 3, +ve signal		
D3-B	22	I/O	Port B, Channel 3, -ve signal		
SCL_B	40	I/O	Port B, DDC Clock		
SDA_B	39	I/O	Port B, DDC Data		
HPD_B	21	I/O	Port B, Hot Plug Detects		
CEC_B	20	I/O	Port B, Consumer Electronics Control		
D0+	5	I/O	Common Port, Channel 0, +ve signal		
D0-	6	I/O	Common Port, Channel 0, -ve signal		
D1+	7	I/O	Common Port, Channel 1, +ve signal		
D1-	8	I/O	Common Port, Channel 1, -ve signal		
D2+	10	I/O	Common Port, Channel 2, +ve signal		
D2-	11	I/O	Common Port, Channel 2, -ve signal		
D3+	12	I/O	Common Port, Channel 3, +ve signal		
D3-	13	I/O	Common Port, Channel 3,-ve signal		
SCL	3	I/O	Common Port, DDC Clock		
SDA	4	I/O	Common Port, DDC Data		
HPD	14	I/O	Common Port, Hot Plug Detects		
CEC	15	I/O	Common Port, Consumer Electronics Control		
NC	9, 30	NC	No Connect		
GND	PowerPad	GND	Ground		



#### 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage range		-0.5	5.5	V
V <sub>I/O</sub>	Analog voltage range (2)(3)(4)	All I/O	-0.5	5.5	V
$V_{IN}$	Digital input voltage range (2)(3)	SEL1, SEL2, EN	-0.5	5.5	V
I <sub>I/OK</sub>	Analog port diode current	V <sub>I/O</sub> < 0		-50	mA
I <sub>IK</sub>	Digital input clamp current	V <sub>IN</sub> < 0		-50	mA
I <sub>I/O</sub>	On-state switch current <sup>(5)</sup>		-128	128	mA
T <sub>stg</sub>	Storage temperature range		-65	150	°C

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- 2) All voltages are with respect to ground, unless otherwise specified.
- (3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (4)  $V_I$  and  $V_O$  are used to denote specific conditions for  $V_{I/O}$ .
- (5) I<sub>I</sub> and I<sub>O</sub> are used to denote specific conditions for I<sub>I/O</sub>.

#### 6.2 ESD Ratings

				VALUE	UNIT
			Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, (1)	±2000	
V	(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101,	±1000	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

#### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
$V_{CC}$	Supply voltage	2.6	4.5	V
$V_{I/O}$	Input/Output voltage	0	5.5	V
T <sub>A</sub>	Operating free-air temperature	-40	85	°C

<sup>(1)</sup> All unused control inputs of the device must be held at VDD or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

#### 6.4 Thermal Information

		TS3DV642	
	THERMAL METRIC <sup>(1)</sup>	RUA	UNIT
		42 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	31.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	16.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	5.5	°C/W
ΨJT	Junction-to-top characterization parameter	0.2	°C/W
ΨЈВ	Junction-to-board characterization parameter	5.4	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	2.0	°C/W

 For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



#### 6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER		TEST CONDITIONS <sup>(1)</sup>	MIN TYP <sup>(2)</sup>	MAX	UNIT
PORT A						
Б	ON state weststance	D0 to D3	$V_{CC} = 3 \text{ V}, 1.5 \text{ V} \le V_{I/O} \le V_{CC}$	6.5	9.5	Ω
R <sub>ON</sub>	ON-state resistance	SCL, SDA, HPD, CEC	$I_{I/O} = -40 \text{ mA}$	6	9.5	Ω
R <sub>ON(flat)</sub> <sup>(3)</sup>	ON-state resistance flatness	All I/O	$V_{CC}$ = 3 V, $V_{I/O}$ = 1.5 V and $V_{CC}$ , $I_{I/O}$ = -40 mA	1.5		Ω
$\Delta R_{ON}^{(4)}$	On-state resistance match between high-speed channels	D0 to D3	$VCC = 3 \text{ V}, 1.5 \text{ V} \le \text{VI/O} \le \text{V}_{CC},$ $\text{I}_{\text{I/O}} = -40 \text{ mA}$	0.4	1	Ω
I <sub>OFF</sub>	Leakage under power off	All outputs	$V_{CC} = 0 \text{ V}, V_{I/O} = 0 \text{ to } 3.6 \text{ V}, V_{IN} = 0 \text{ V to } 5.5 \text{ V}$		±10	μΑ
PORT B				*	'	-
D	ON state weststands	D0 to D3	$V_{CC} = 3 \text{ V}, 1.5 \text{ V} \le V_{I/O} \le V_{CC},$	8.2	10.5	Ω
R <sub>ON</sub>	ON-state resistance	SCL, SDA, HPD, CEC	II/O = -40 mA	6	9.5	Ω
R <sub>ON(flat)</sub> (3)	ON-state resistance flatness	All I/O	$V_{CC}$ = 3 V, $V_{I/O}$ = 1.5 V and $V_{CC}$ , $I_{I/O}$ = -40 mA	1.5		Ω
$\Delta R_{ON}^{(4)}$	On-state resistance match between high-speed channels	D0 to D3	$V_{CC} = 3 \text{ V, } 1.5 \text{ V} \le V_{I/O} \le V_{CC},$ $I_{I/O} = -40 \text{ mA}$	0.4	1	Ω
I <sub>OFF</sub>	Leakage under power off	All outputs	$V_{CC} = 0 \text{ V}, V_{I/O} = 0 \text{ V to } 3.6 \text{ V}, V_{IN} = V \text{ to } 5.5 \text{ V}$		±10	μΑ
DIGITAL II	NPUTS (SEL1, SEL2, EN)			*	,	
V <sub>IH</sub>	High-level control input voltage	SEL1, SEL2, EN		1.4		V
V <sub>IL</sub>	Low-level control input voltage	SEL1, SEL2, EN			0.5	V
I <sub>IH</sub>	Digital input high leakage current	SEL1, SEL2, EN	$V_{CC} = 3.6 \text{ V}$ , $V_{IN} = V_{DD}$		±10	μΑ
I <sub>IL</sub>	Digital input low leakage current	SEL1, SEL2, EN	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = GND		±10	μΑ
SUPPLY						
I <sub>CC</sub>	VCC supply current		V <sub>CC</sub> = 3.6 V, I <sub>I/O</sub> = 0, Normal Operation Mode, EN = H	50		μΑ
I <sub>CC</sub> , PD	VCC supply current in power	er-down mode	$V_{CC} = 3.6 \text{ V}, I_{I/O} = 0, EN = L$	6		μA

 $<sup>\</sup>begin{array}{lll} \text{(1)} & V_{\text{I}}, \ V_{\text{O}}, \ I_{\text{I}}, \ \text{and} \ I_{\text{O}} \ \text{refer} \ \text{to} \ \text{I/O} \ \text{pins}, \ V_{\text{IN}} \ \text{refers} \ \text{to} \ \text{the} \ \text{control} \ \text{inputs}. \\ \text{(2)} & \text{All typical values are at} \ V_{\text{CC}} = 3.3 \ \text{V} \ \text{(unless otherwise noted)}, \ T_{\text{A}} = 25^{\circ}\text{C}. \\ \text{(3)} & R_{\text{ON}(\text{FLAT})} \ \text{is} \ \text{the} \ \text{difference} \ \text{of} \ R_{\text{ON}} \ \text{in} \ \text{a} \ \text{given} \ \text{channel} \ \text{at specified voltages}. \\ \text{(4)} & \Delta R_{\text{ON}} \ \text{is} \ \text{the} \ \text{difference} \ \text{of} \ \text{RON} \ \text{from} \ \text{center} \ \text{port} \ \text{to} \ \text{any} \ \text{other ports}. \\ \end{array}$ 



#### 6.6 Dynamic Characteristics

Over recommended operation free-air temperature range,  $V_{CC} = 3.3V \pm 0.3V$  (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT	
C <sub>IN</sub>	Digital input capacitand	е	f = 1 MHz, V <sub>IN</sub> = 0 V		6		pF	
Coff	Switch OFF capacitano	e	$f = 1 \text{ GHz}$ , $V_{I/O} = 0 \text{ V}$ , Output is open, Switch is OFF		0.3		pF	
Con	Switch ON capacitance	)	$f = 1 \text{ GHz}$ , $V_{I/O} = 0 \text{ V}$ , Output is open, Switch is ON		0.5		pF	
	Xtalk Differential Crosstalk		$R_L = 50 \Omega$ at 1.7 GHz (See Figure 17)		-40			
Xtalk			$R_L$ = 50 $\Omega$ at 2.7 GHz (See Figure 17)		-40		dB	
			$R_L = 50 \Omega$ at 4.05 GHz (See Figure 17)		-35			
			$R_L = 50 \Omega$ at 1.7 GHz (See Figure 18)		-23		dB	
OISO	Differential Off Isolation	1	$R_L = 50 \Omega$ at 2.7 GHz (See Figure 18)		-28			
			$R_L = 50 \Omega$ at 4.05 GHz (See Figure 18)		-25			
	Language Language		Port A at DC		-0.75		JD	
IL	IL Insertion Loss		Port B at DC		-1		dB	
DW	Differential Bandwidth	Port A	$R_L = 50 \Omega$ , All channels (See Figure 19)		6.9		CLI-	
BW	(-3 dB)	Port B	$R_L = 50 \Omega$ , All channels (See Figure 19)		7.5		GHz	

<sup>(1)</sup> All Typical Values are at  $V_{CC}$  = 3.3 V (unless otherwise noted),  $T_A$  = 25°C.

## 6.7 Switching Characteristics

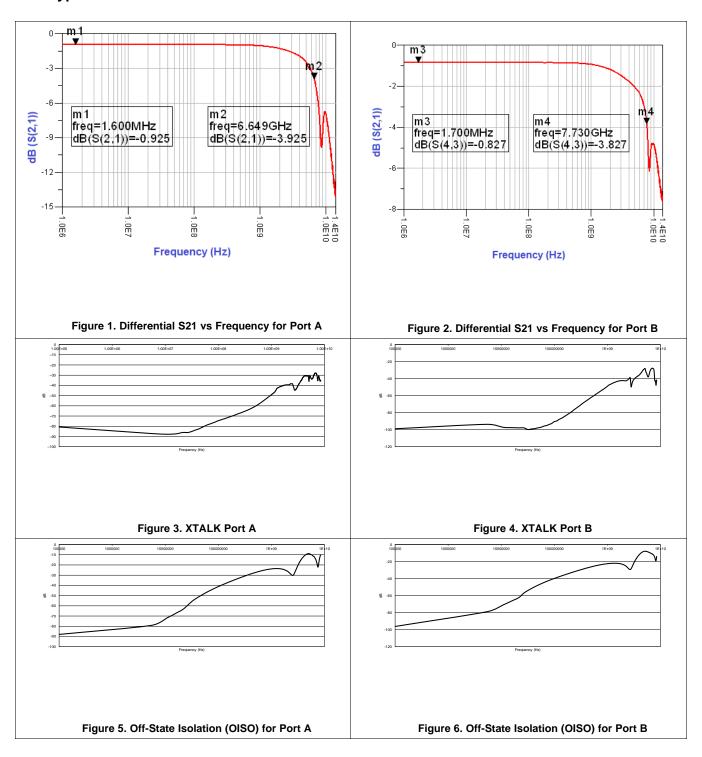
over recommended operation free-air temperature range,  $V_{CC}$  = 3.3 V± 0.3 V (unless otherwise noted)

	PARAME	TER		TEST CONDITIONS	MIN TYP(1)	MAX	UNIT	
t <sub>ON</sub> (2)	Switch turn-on time		All I/O	See Figure 14		100	μs	
t <sub>SWITCH</sub> (3)	Switching time between	en channels	All I/O	See Figure 15	20		μs	
			D0 to D3		30			
_	Dranagation Dalou	Port A	SCL, SDA, HPD, CEC	See Figure 46	30			
t <sub>pd</sub>	Propagation Delay		D0 to D3	See Figure 16	40 30		ps	
		Port B	SCL, SDA, HPD, CEC					
	latan main Olyany	Port A		Between +ve and -ve signals of	2			
	Inter-pair Skew	Port B	D0 to D2	each Channel	2			
t <sub>SKEW</sub>	Intro poir Cleave	Port A	D0 to D3	Detugen Channel 0, 1, 2, or 2	2		ps	
	Intra-pair Skew	Port B		Between Channel 0, 1, 2, or 3	6			

<sup>(1)</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  (unless otherwise noted),  $T_A = 25^{\circ}\text{C}$ . (2)  $t_{ON}$  is the time it takes the output to recover after enabling switches (3)  $t_{SWITCH}$  is the time it takes for the output to recover after the state is changed



#### 6.8 Typical Characteristics

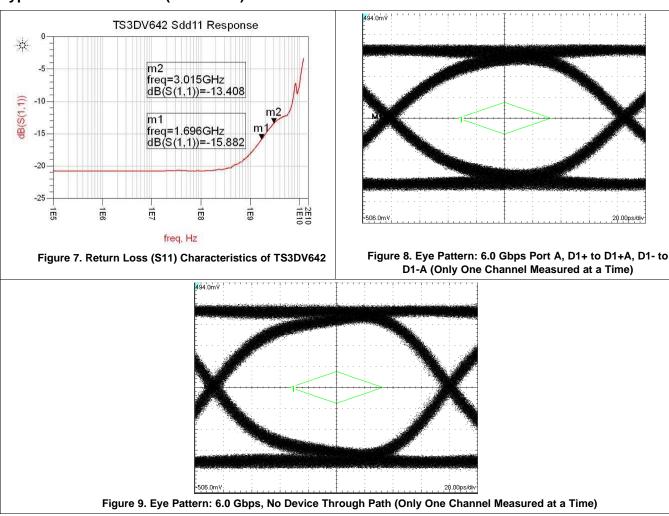


Product Folder Links: TS3DV642

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## TEXAS INSTRUMENTS

#### **Typical Characteristics (continued)**



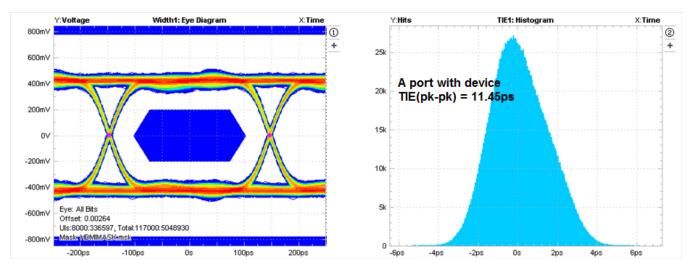


Figure 10. Eye Pattern and Time Interval Error Histogram: 3.4 Gbps Port A, With Device



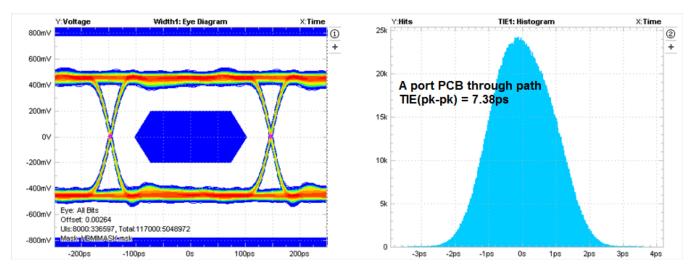


Figure 11. Eye Pattern and Time Interval Error Histogram: 3.4 Gbps, No Device Through Path

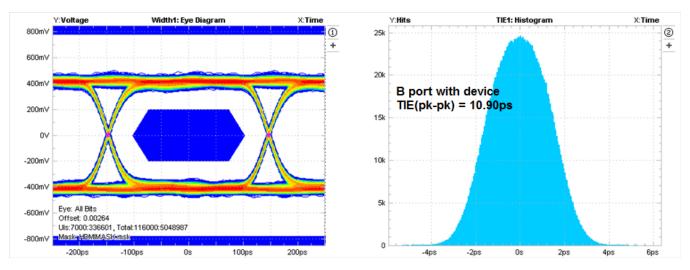


Figure 12. Eye Pattern and Time Interval Error Histogram: 3.4 Gbps Port B, With Device

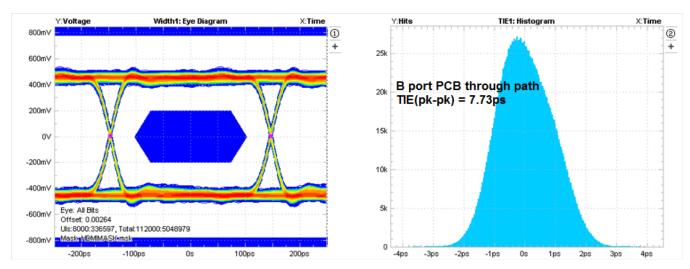
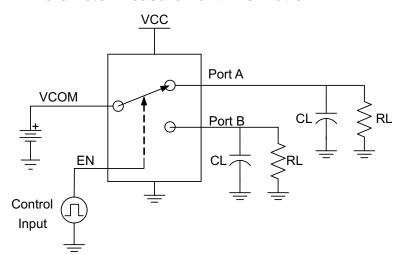


Figure 13. Eye Pattern and Time Interval Error Histogram: 3.4 Gbps Port B, No Device



## 7 Parameter Measurement Information



RL	CL	Vсом
50 Ω	4 pF	Vcc

\*CL includes probe, cable, and board capacitance

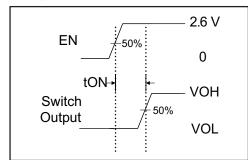
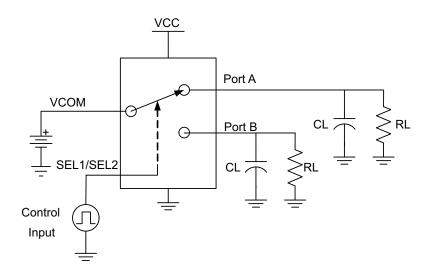


Figure 14. Switch Turn-On Time (ton)



RL	CL	VCOM
50 Ω	4 pF	Vcc

\*CL includes probe, cable, and board capacitance

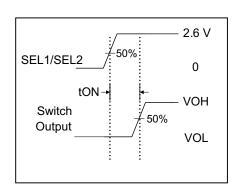
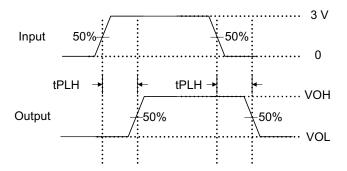


Figure 15. Switching Time Between Channels (t<sub>SWITCH</sub>)



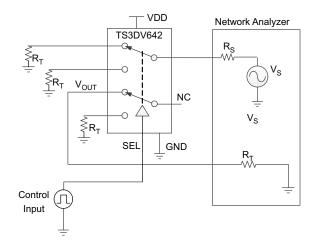
tpd = (tPLH + tPLH)/2

Figure 16. Propagation Delay (tpd)

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#### **Parameter Measurement Information (continued)**



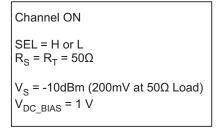
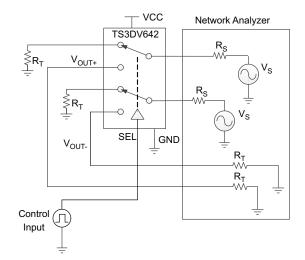


Figure 17. Crosstalk (Xtalk)



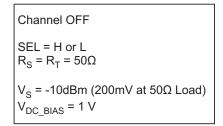
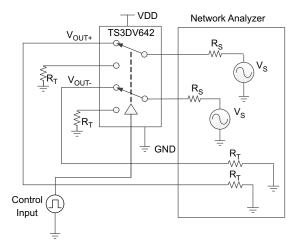


Figure 18. Differential Off-Isolation (OISO)



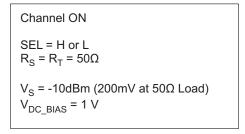


Figure 19. Differential Bandwidth (BW)

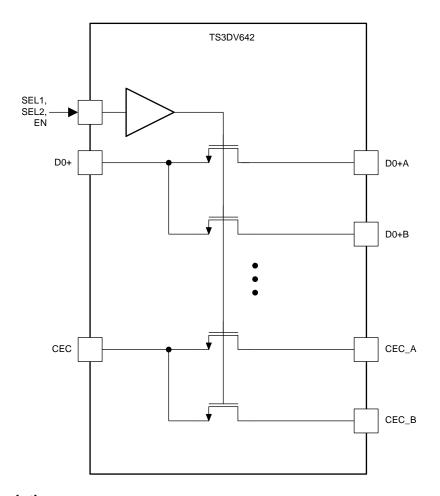


#### 8 Detailed Description

#### 8.1 Overview

TS3DV642 is a 12-channel 1:2 or 2:1 bidirectional multiplexer/demultiplexer. The TS3DV642 operates from a 2.6 to 4.5 V supply, making it suitable for battery-powered applications. It offers low and flat on-state resistance as well as low I/O capacitance which allows it to achieve a typical bandwidth of up to 7.5 GHz. The device provides the high bandwidth necessary for HDMI and DisplayPort applications.

#### 8.2 Functional Block Diagram



#### 8.3 Feature Description

The TS3DV642 is based on proprietary TI technology which uses FET switches driven by a high-voltage generated from an integrated charge-pump to achieve a low on-state resistance. TS3DV642 has 12-channel bidirectional switches with a high bandwidth (~ 7.5 GHz). TS3DV642 uses an extremely low power technology and uses only 50  $\mu$ A  $I_{CC}$  in active mode. The device has integrated ESD that can support up to 2-kV Human-Body Model (HBM) and 1-kV Charge Device Model (CDM). TS3DV642 is offered in a 42-pin QFN package (9 mm x 3.5 mm) with 0.5 mm pitch. The device can support analog I/O signal in 0 to 5 V range. TS3DV642 also has a special feature that prevents the device from back-powering when the  $V_{CC}$  supply is not available and an analog signal is applied on the I/O pin. In this situation this special feature prevents leakage current in the device. The TS3DV642 is not designed for passing signals with negative swings; the high-speed signals need to be properly DC biased (usually ~1 V) before being passed to the TS3DV642. The differential S21 characteristics as a function of frequency for Port A and Port B are shown in Figure 1 and Figure 2, respectively. The figures show a differential bandwidth of 6.7 GHz and 7.7 GHz for Port A and Port B, respectively. The cross-talk (XTALK) characteristics as a function of frequency are shown in Figure 3 and Figure 6, respectively. The return loss



#### **Feature Description (continued)**

characteristics (S11) are shown in Figure 7. The eye pattern and Time Interval Error (TIE) histogram at 3.4 Gbps (for HDMI 1.4 applications) with TS3DV642 in path for Port A is shown in Figure 10. The eye pattern and Time Interval Error (TIE) histogram at 3.4 Gbps through path (no TS3DV642) for Port A is shown in Figure 11. The eye pattern and Time Interval Error (TIE) histogram at 3.4 Gbps (for HDMI 1.4 applications) with TS3DV642 in path for Port B is shown in Figure 12. The eye pattern and Time Interval Error (TIE) histogram at 3.4 Gbps through path (no TS3DV642) for Port A is shown in Figure 13. The eye pattern at 6.0 Gbps (for HDMI 2.0 applications) with TS3DV642 in path for Port A is shown in Figure 8. The eye pattern at 6.0 Gbps (for HDMI 2.0 applications) through path (no TS3DV642) for Port A is shown in Figure 9. Note that the eye patterns are measured with only one channel on at a time.

#### 8.4 Device Functional Modes

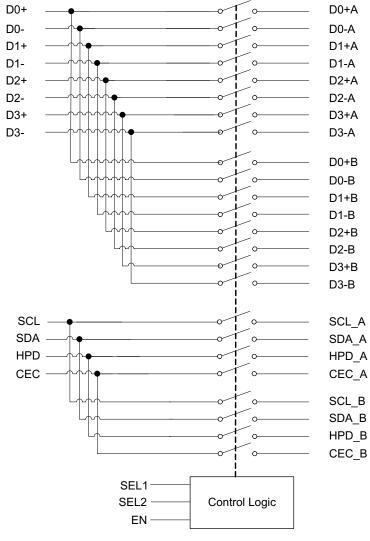


Figure 20. Logic Diagram



## **Device Functional Modes (continued)**

Table 1 lists the device functions for the TS3DV642 device.

#### **Table 1. Functional Table**

EN	SEL1	SEL2	FUNCTION
L	X	X	Switch disabled. All channels are Hi-Z.
Н	L	L	Channel D0+/D0- to D0+A/D0-A is ON. All the other channels (D1+/D1-, D2+/D2-, D3+/D3-, SCL, SDA, HPD, CEC) are Hi-Z.
Н	L	Н	Channel D0+/D0- to D0+B/D0-B is ON. All the other channels (D1+/D1-, D2+/D2-, D3+/D3-, SCL, SDA, HPD, CEC) are Hi-Z.
Н	Н	L	All A channels are enabled. All B channels are Hi-Z.
Н	Н	Н	All B channels are enabled. All A channels are Hi-Z.



#### 9 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 9.1 Application Information

TS3DV642 can be used for two typical DisplayPort applications. Figure 21 describes a DisplayPort (DP) application where TS3DV642 is used to switch between two different graphic & memory controllers on a single DP connector. Figure 24 shows a docking application where TS3DV642 is used to switch signals from a single graphic and memory controller to a display port and docking station connector. Note that the TS3DV642 is not designed for passing signals with negative swings; the high-speed signals need to be properly DC biased (usually ~1 V from the graphic controller side) before being passed to the TS3DV642.

#### 9.2 Typical Application

#### 9.2.1 Display Port (DP) Application

Display port (DP) application with TS3DV642 used to switch between two different graphic & memory controllers on a single DP connector

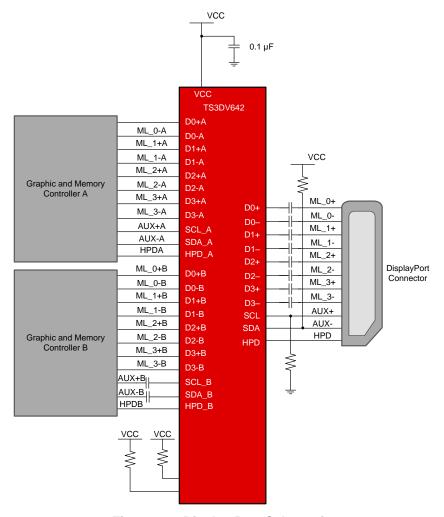


Figure 21. Display Port Schematic



#### **Typical Application (continued)**

#### 9.2.1.1 Design Requirements

Table 2. Design parameters for Display Port application

Design parameter	Example value
V <sub>CC</sub>	2.6 V to 4.5 V
VCC decoupling capacitor	0.1 μF
MainLink (ML) and AUX coupling capacitor	75 nF to 200 nF
AUX Pull-up / Pull-down resistors	10 kΩ to 100 kΩ
Pull-up / Pull-down resistors for SEL1 / SEL2 pins	10 kΩ

#### 9.2.1.2 Detailed Design Procedure

The TS3DV642 is designed to operate with 2.6 V - 4.5 V power supply. The wide power supply range allows flexibility for battery powered applications. If a higher power supply is used in the system, a voltage regulator can be used to bring down the voltage to 2.6 V - 4.5 V range. Decoupling capacitors may be used to reduce noise and improve power supply integrity. AC coupling capacitors in 75 nF - 200 nF range must be placed on the MainLink (ML) and AUX lanes. In this particular application the AC coupling capacitors are shown on the connector side. The AC coupling capacitors may also be placed on the signal path on controller side. The AUX+ line must be pulled-down weakly through a resistor to ground and the AUX- line must be pulled-up weakly through a resistor to VCC.

#### 9.2.1.3 Application Curves

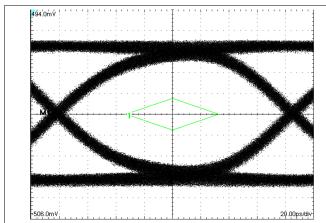


Figure 22. Eye Pattern: 6.0 Gbps Port A, D1+ to D1+A, D1to D1-A (Only One Channel Measured at a Time)

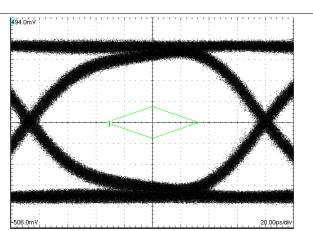


Figure 23. Eye Pattern: 6.0 Gbps, No Device Through Path (Only One Channel Measured at a Time)

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#### 9.2.2 Docking Application

Docking Application with TS3DV642 used to switch signals from a single graphic and memory controller to a display port and docking station connector.

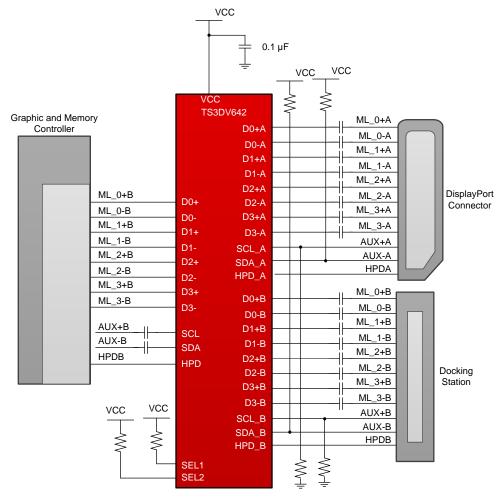


Figure 24. Docking Application Schematic

#### 9.2.2.1 Design Requirements

Table 3. Design parameters for docking application

Design parameter	Example value
V <sub>CC</sub>	2.6 V to 4.5 V
VCC decoupling capacitor	0.1 μF
MainLink (ML) and AUX coupling capacitor	75 nF to 200 nF
AUX Pull-up / Pull-down resistors	10 kΩ to 100 kΩ
Pull-up / Pull-down resistors for SEL1 / SEL2 pins	10 kΩ



#### 9.2.2.2 Detailed Design Procedure

The TS3DV642 is designed to operate with 2.6 V - 4.5 V power supply. The wide power supply range allows flexibility for battery powered applications. If a higher power supply is used in the system, a voltage regulator can be used to bring down the voltage to 2.6 V - 4.5 V range. Decoupling capacitors may be used to reduce noise and improve power supply integrity. AC coupling capacitors in 75 nF - 200 nF range must be placed on the MainLink (ML) and AUX lanes. In this particular application the AC coupling capacitors are shown on the connector side. The AC coupling capacitors may also be placed on the signal path on controller side. The AUX+ line must be pulled-down weakly through a resistor to ground and the AUX- line must be pulled-up weakly through a resistor to VCC.

#### 9.2.2.3 Application Curves

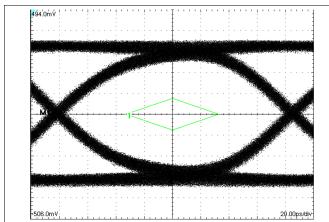


Figure 25. Eye Pattern: 6.0 Gbps Port A, D1+ to D1+A, D1to D1-A (Only One Channel Measured at a Time)

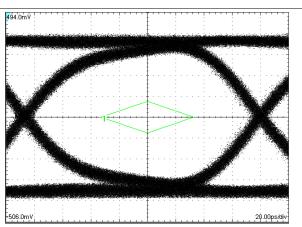


Figure 26. Eye Pattern: 6.0 Gbps, No Device Through Path (Only One Channel Measured at a Time)

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#### 9.2.3 HDMI Application

HDMI Application with TS3DV642 used to switch signals from a single graphic and memory controller to a two HDMI connectors.

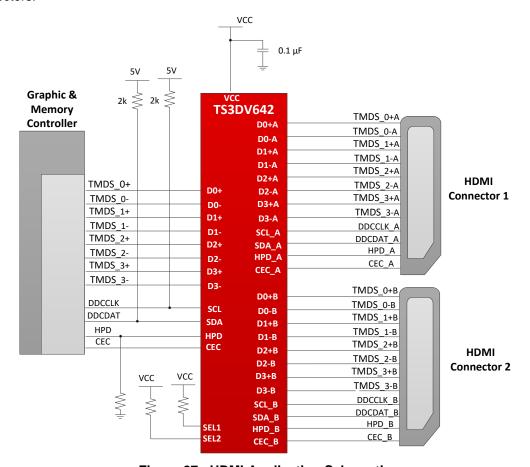


Figure 27. HDMI Application Schematic

#### 9.2.3.1 Design Requirements

**Table 4. Design Parameters for HDMI Application** 

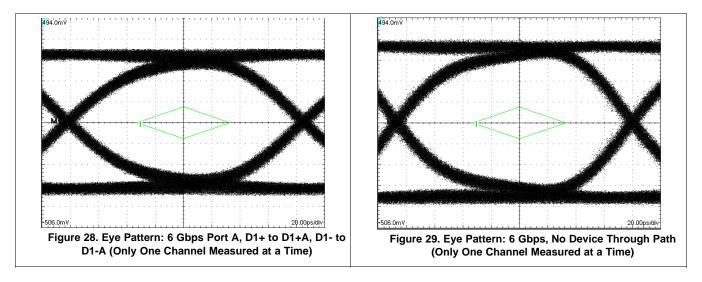
Design parameter	Example value
V <sub>CC</sub>	2.6 V to 4.5 V
VCC decoupling capacitor	0.1 μF
DDC Pull-up resistors	2 kΩ to 5 V
Pull-up / Pull-down resistors for SEL1 / SEL2 pins	10 kΩ
HPD Pull-down resistor	100 kΩ

#### 9.2.3.2 Detailed Design Procedure

The TS3DV642 is designed to operate with 2.6 V - 4.5 V power supply. The wide power supply range allows flexibility for battery powered applications. If a higher power supply is used in the system, a voltage regulator can be used to bring down the voltage to 2.6 V - 4.5 V range. Decoupling capacitors may be used to reduce noise and improve power supply integrity. Pull-up resistors to 5 V must be placed on the source side DDC clock and data lines according to the HDMI standard. A weak pull-down resistor must be placed on the source side HPD line.



#### 9.2.3.3 Application Curves



## 10 Power Supply Recommendations

 $V_{CC}$  should be in the range of 2.6 V to 4.5 V. Voltage levels above those listed in the Absolute Ratings table should not be used. Decoupling capacitors may be used to reduce noise and improve power supply integrity. There are no power sequence requirements for the TS3DV642.



#### 11 Layout

#### 11.1 Layout Guidelines

To ensure reliability of the device, the following commonly used printed-circuit board layout guidelines are recommended:

- Decoupling capacitors should be used between power supply pin and ground pin to ensure low impedance to reduce noise To achieve a low impedance over a wide frequency range use capacitors with a high selfresonance frequency.
- ESD and EMI protection devices (if used) should be placed as close as possible to the connector.
- Short trace lengths should be used to avoid excessive loading.
- To minimize the effects of crosstalk on adjacent traces, keep the traces at least two times the trace width apart.
- Separate high-speed signals from low-speed signals and digital from analog signals
- Avoid right-angle bends in a trace and try to route them at least with two 45° corners.
- The high-speed differential signal traces should be routed parallel to each other as much as possible. The traces are recommended to be symmetrical.
- A solid ground plane should be placed next to the high-speed signal layer. This also provides an excellent low-inductance path for the return current flow.



#### 11.2 Layout Example

TS3DV642 application with a single controller interfacing with two HDMI connectors.

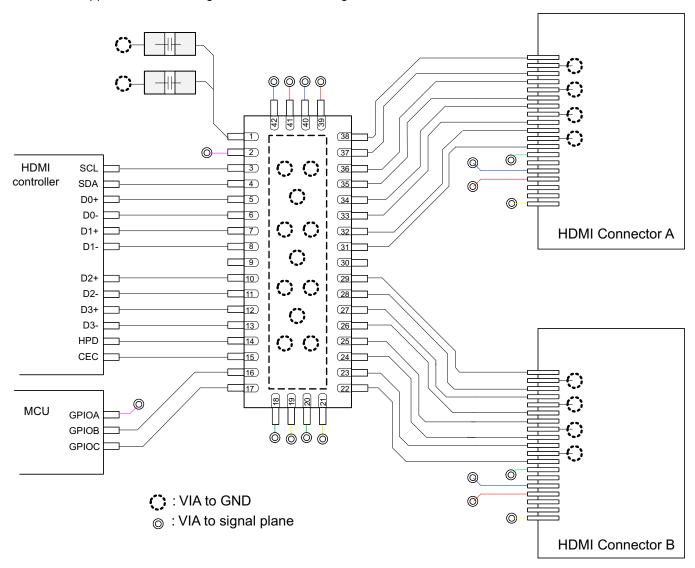


Figure 30. Layout Example



#### 12 Device and Documentation Support

#### 12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.3 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

#### 12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 21-Mar-2021

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
TS3DV642A0RUAR	ACTIVE	WQFN	RUA	42	3000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	SD642A0	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF TS3DV642:

## **PACKAGE OPTION ADDENDUM**

www.ti.com 21-Mar-2021

Automotive : TS3DV642-Q1

NOTE: Qualified Version Definitions:

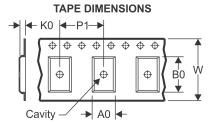
• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

## PACKAGE MATERIALS INFORMATION

www.ti.com 17-Aug-2018

## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3DV642A0RUAR	WQFN	RUA	42	3000	330.0	16.4	3.8	9.3	1.0	8.0	16.0	Q1

www.ti.com 17-Aug-2018



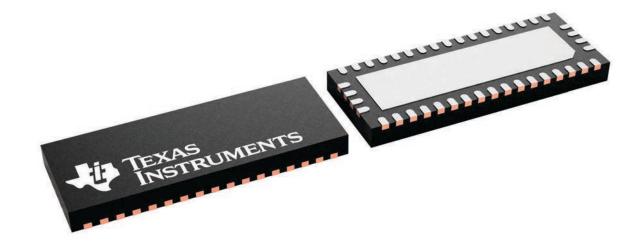
#### \*All dimensions are nominal

Device Package Type		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TS3DV642A0RUAR	WQFN	RUA	42	3000	367.0	367.0	38.0	

9 x 3.5, 0.5 mm pitch

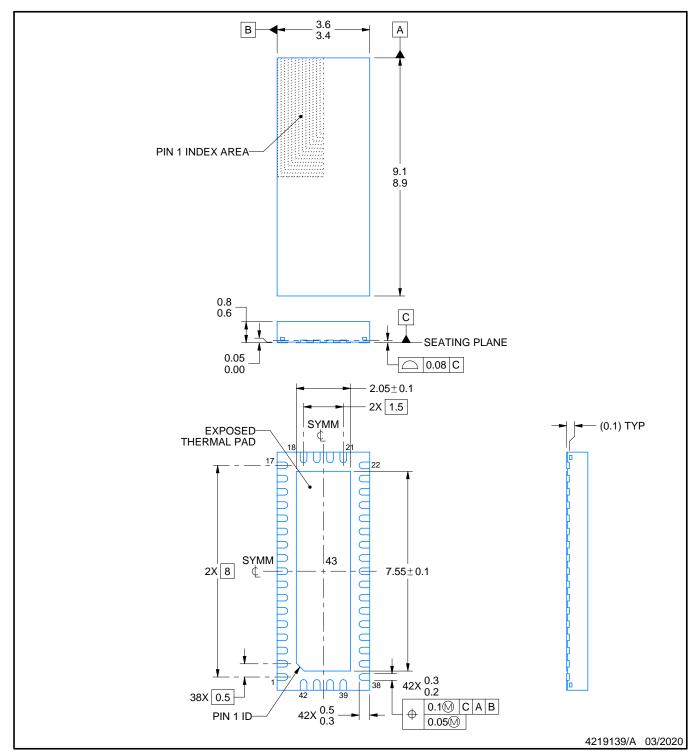
PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





PLASTIC QUAD FLATPACK - NO LEAD

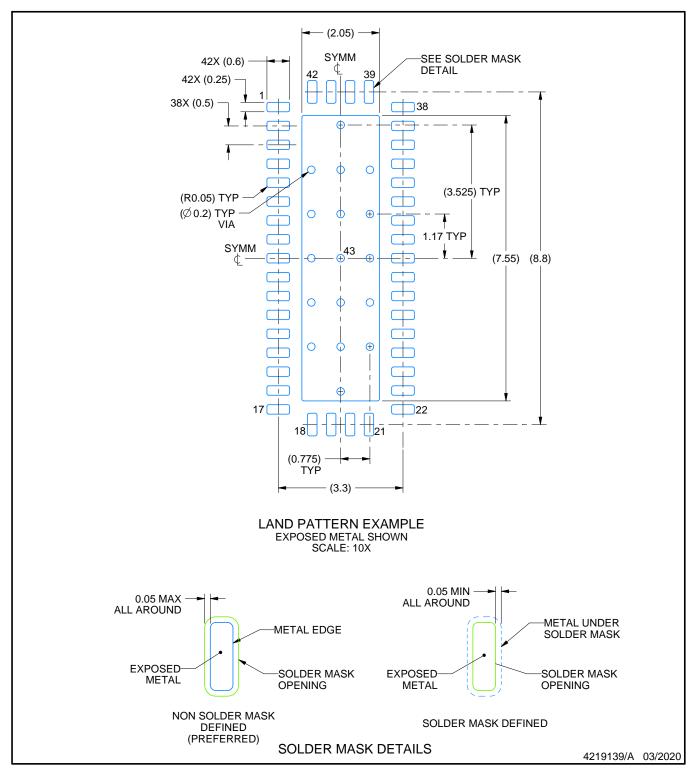


#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

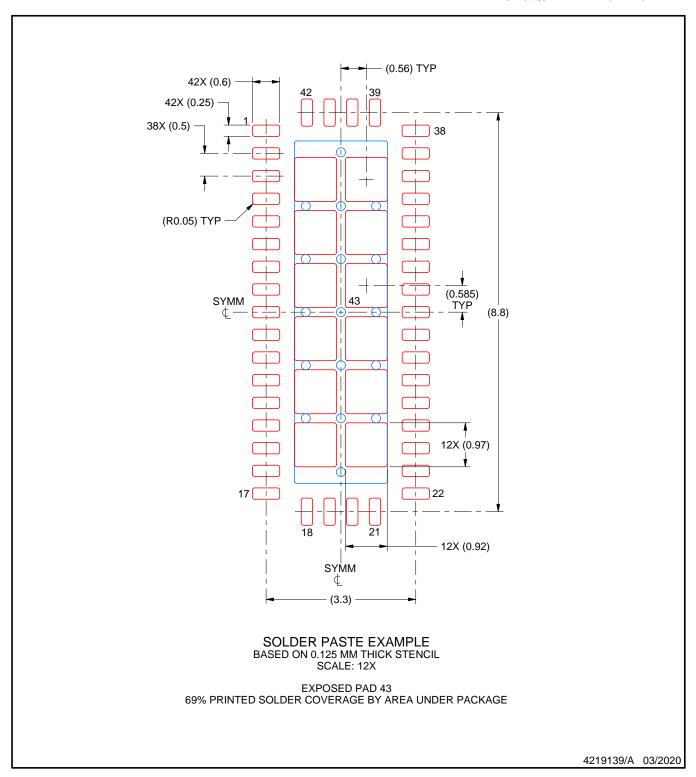


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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